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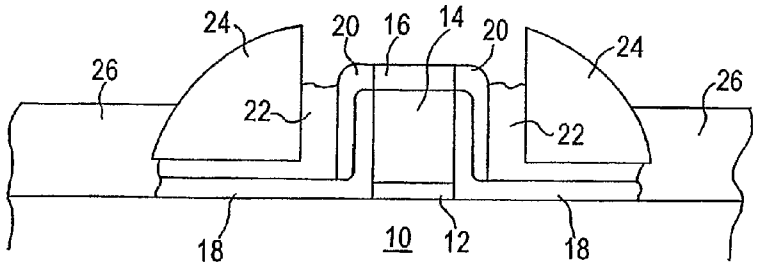
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(54) **Title:** A RAISED SOURCE AND DRAIN PROCESS WITH DISPOSABLE SPACERS



(57) **Abstract:** A method for forming raised source and drain regions (26, 48) in a semiconductor manufacturing process employs double disposable spacers (20, 24; 40, 46). A deposited oxide (22, 42) is provided between the first and second disposable spacers (20, 24; 40, 46), and serves to protect the gate electrode (14, 34), first disposable spacers (20, 40) and a cap layer (16, 36) during the dry etching of the larger, second disposable spacers (24, 46). Mouse ears are thereby prevented, while the use of a second disposable spacer (24, 46) avoids shadow-effects during halo ion- implants.

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